Multiple Dirac Nodes and Symmetry Protected Dirac Nodal Line in Orthorhombic $\alpha$-RhSi

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Owing to their chiral cubic structure, exotic multifold topological excitations have been predicted and recently observed in transition metal silicides like $\beta$-RhSi. Herein, we report that the topological character of RhSi is also observed in its orthorhombic $\alpha$-phase which displays multiple types of Dirac nodes very close to the Fermi level ($\varepsilon_F$) with the near absence of topologically trivial carriers.

Dirac semimetals, which in contrast to Weyl systems preserve Kramers degeneracy, have also attracted a lot of attention recently. Compounds like Cd$_3$As$_2$ unveiled, for example, a possible novel mechanism of topological protection against backscattering or, upon lifting time reversal symmetry and hence Kramers degeneracy, evidence for the chiral anomaly among field-induced Weyl nodes in Na$_3$Bi. This splitting of the Dirac into Weyl nodes has led to the prediction and subsequent observation of new cyclotron orbits involving Fermi arcs on the surface of Cd$_3$As$_2$ with an associated quantum Hall effect. Topological nodal line (NL) systems, or systems where two bands cross forming closed lines within the BZ, is another very active area of research. In general, spin-orbit coupling gaps the NLs unless they are protected by some crystalline symmetry in addition to the inversion and time-reversal symmetry. Prominent examples include the family of the ZrSiS compounds that display Dirac NLs resulting from the intersection of Dirac-like dispersing bands at both symmetric and nonsymmetric positions and the correlated Dirac NL iridate CaIrO$_3$.

Here, we report through group theory analysis and Density Functional Theory (DFT) calculations the existence of Dirac nodes and double Dirac nodes near high symmetry points, and very close to $\varepsilon_F$, in $\alpha$-RhSi, which adopts the orthorhombic MnP (B31) structure type (centrosymmetric space group $Pmna$, No. 62). The intersection between the Dirac dispersions emerging from the double Dirac node leads to a symmetry protected Dirac nodal line. DFT calculations are confirmed via measurements of the dHvA-effect in flux grown crystals which unveils a Fermi surface whose topography is in good agreement with the predictions. For certain field orientations, the magnetic torque unveils an anomalous back-
tinct $T$s we estimate the carrier concentrations $n_{e,h}$ and their mobilities $\mu_{e,h}$ through a two-band analysis. Mobilities and carrier concentrations are observed to increase as $T$ is lowered with this system behaving as a compensated semimetal. More importantly, at $T = 2$ K one extracts high mobilities for holes, i.e. $\mu_h = 3727$ cm$^2$/Vs and electrons $\mu_e = 2491$ cm$^2$/Vs thus confirming the high quality of our single crystals. If instead, one evaluated the mean transport mobility from the Hall-effect, as shown in Fig. S3 one obtains $\mu_{tr} \simeq 6667$ cm$^2$/Vs at $T = 2$ K, further confirming that our flux grown crystals display a very low density of defects.

Figure 1 (b) displays the magnetic torque $\tau = (\mu_0 H)\Delta M \sin \theta/2$, where $\Delta M$ is the anisotropy in the magnetization $M_{c,ab} = \chi_{c,ab}(\mu_0 H)$ ($\chi_i$ is the susceptibility along the $i$-axis) for a layered system, as a function of magnetic field $\mu_0 H$ and for three different angles $\theta$ between $\mu_0 H$ and the (100) plane of the crystal. $\tau$ is expected to behave as $\propto (\mu_0 H)^2$ as illustrated by the fit (red line) to the $\tau(\mu_0 H)$ trace collected at $\theta = 74.2^\circ$. The superimposed oscillatory component corresponds to the dHvA-effect resulting from the Landau quantization of the electronic spectrum. In contrast, at low angles the background of $\tau(\mu_0 H)$ can only be fitted to non-physical combinations of quadratic and quartic terms. This sharp change in the behavior of $\tau(\mu_0 H)$ cannot be reconciled with the diamagnetic response of this system. Therefore, it suggests the possibility of either topological phase-transitions or crossovers between distinct topological regimes induced by the Zeeman-effect. Below we provide the band structure calculations revealing a double Dirac structure whose nodes are very close in energy and hence susceptible to the energy scale of the external field.

In Fig. 2 we show the BZ, its high symmetry points, and the electronic band structure of orthorhombic $\alpha$-RhSi. See also Fig. S4 for the band structure depicted over the entire BZ. Its various panels show that there are four-fold symmetries and the presence of several band crossings. These crossings along various high symmetry directions can be understood from a symmetry analysis as presented next. We will mainly focus on the $S$ high-symmetry point because there are band crossings near the Fermi level. We also show that there should be a nodal line on the $k_y - k_z$ high-symmetry plane which is caused by these band crossings. The close proximity in energy between these band crossings, that are within the resolution of DFT, requires an independent verification for their existence hence the subsequent group symmetry analysis.

The space group $Pnma$ (No. 62) is a non-symmorphic space group $^{43}$ with three screw-axis symmetry operations of the general form using Seitz notation: $\{200\{1\bar{1}1\}\}, \{2010\{0\bar{2}0\}\}, \{2001\{1\bar{0}\bar{1}\}\}$, and the three glide-plane symmetry operations: $\{m_{100}\{1\bar{2}1\}\}, \{m_{010}\{0\bar{2}0\}\}, \{m_{001}\{1\bar{0}\bar{2}\}\}$. There are also time-reversal symmetry (TRS) and inversion symmetry which yield Kramers degeneracy. The band-representations of the double space
group 62 at the various high symmetry points of the Brillouin zone for the Wyckoff position $6d: (x, y, z)$ (the case for $\alpha$-RhSi) are known\textsuperscript{44–46} and can be found in the Bilbao Crystallographic Server\textsuperscript{47}.

The representations of the subgroups of the high-symmetry points (HSPs) $R$, $S$, and $U$, are direct sums of the two four-dimensional (4D) representations that includes Kramers degeneracy. Due to this additional degeneracy they consist of either a pair of the same irreducible representations (e.g., $R_3R_3$) or different irreducible representations (e.g., $R_3R_4$). At the $\Gamma$ point there is no such additional degeneracy. These are irreducible representations (IR) of the little group corresponding to each high-symmetry $k$-point and they are subduced along high-symmetry lines that connects them. For example, along the $RS$ high-symmetry manifold, since the symmetry is lower than that of the high-symmetry points that it connects, the IR $R_3R_3$ and $R_4R_4$ become reducible to

$$R_3R_3 \rightarrow Q_3Q_3(2) \oplus \bar{Q}_5\bar{Q}_5(2), \quad (1)$$
$$R_4R_4 \rightarrow \bar{Q}_2\bar{Q}_2(2) \oplus Q_4\bar{Q}_4(2). \quad (2)$$

Similarly, along the same high-symmetry line, the $S_3S_4$ and $S_4S_4$ representations are reducible to

$$S_3S_3 \rightarrow Q_2Q_2(2) \oplus Q_3\bar{Q}_3(2), \quad (3)$$
$$\bar{S}_4\bar{S}_4 \rightarrow Q_4\bar{Q}_4(2) \oplus Q_5\bar{Q}_5(2). \quad (4)$$

Therefore, these IRs along these high symmetry lines connecting the two high symmetry points $S$ and $R$ have to be connected as shown schematically in Fig. 3. The compatible band connectivity, an example of which is shown in Fig. 3(a), for any combination of IRs at the two connected high-symmetry points, forces the intersection of the bands belonging to different $Q$-type IRs and this gives rise to a band crossing along these high-symmetry manifolds. By carrying out the same analysis along the other high-symmetry lines that start from $S$, we are concluding that these crossings form a nodal line.

A somewhat similar band crossing occurs when we consider the break-down of the IRs along the high symmetry lines which start from the high-symmetry point $S$ and they connect the high-symmetry $X$ point ($SX$-line or $D$ manifold) as seen in Fig. 3(b).

The situation along the $SY$ direction is different. Along this symmetry line, the $S_3S_3$ and $S_4S_4$ at the $S$ point become:

$$S_3S_3 \rightarrow \bar{C}_5\bar{C}_5(4), \quad (5)$$
$$\bar{S}_4\bar{S}_4 \rightarrow \bar{C}_5\bar{C}_5(4). \quad (6)$$
And the $\tilde{Y}_3\tilde{Y}_4(4)$ at the $Y$ point becomes
\[ \tilde{Y}_3\tilde{Y}_4(4) \rightarrow \tilde{C}_5\tilde{C}_5(4). \] (7)
Therefore, the $S Y$ line becomes a four-fold degenerate high-symmetry line.

Last, we consider the $\Delta$ manifold, i.e., the line connecting the $\Gamma$ and $Y$ high-symmetry points. Along this direction the IRs at the $Y$ point and $\Gamma$ point reduce as follows:
\[ \tilde{Y}_3\tilde{Y}_4(4) \rightarrow 2\Delta_5(2), \]
\[ \tilde{\Gamma}_5(2) \rightarrow \Delta_5(2), \]
\[ \tilde{\Gamma}_6(2) \rightarrow \Delta_5(2). \] (9)
Therefore, the $\tilde{Y}_3\tilde{Y}_4(4)$ representation, which is irreducible at the $Y$ point, reduces into two 2D representations $\Delta_5(2)$ which can directly connect to a 2D $\tilde{\Gamma}_5(2)$ and a $\tilde{\Gamma}_6(2)$ IRs at the $\Gamma$ point without or with any number of band intersections. The latter seems to be the case in the band structure of $\alpha$-RhSi, namely, the two degenerate bands at the $Y$ point separate along the $Y$ to $\Gamma$ direction and then they intersect each other twice along the $\Delta$ direction before connecting to the $\Gamma$ point (See, Fig. 2(b)). The $S Y$ line is not the only four-fold high-symmetry manifold. The lines $UZ$ ($A$-manifold), $U_X$ ($G$-manifold), $U_R$ ($P$-manifold), and $R_T$ ($E$-manifold) are all four-fold high-symmetry manifolds.

In the previous discussion based on group representation at the high-symmetry points and from their connectivity through high-symmetry lines, we demonstrated that there should be (symmetry-protected) band crossings along high-symmetry lines starting from the $S$ HSP. This also became clear from Fig. 2 where we noticed band crossings along $ST$, $SX$ and $SR$ lines. In fact, in Ref. 30, it was shown that a nonsymmetric symmetry (screw axis) protects a four-band crossing nodal line in systems having both inversion and time-reversal symmetries. This applies directly to our case for the $k_z = \pi$ plane (the plane where our nodal line lies) which is invariant under the screw-axis operator $\{210\}$ $\{111\}$. This implies that there is a symmetry protected nodal line around the $S$ point on the $k_y - k_z$ plane. This is illustrated in Fig. 4(a) where on the $k_y - k_z$ plane there are two upside-down Dirac cones intersecting forming an elliptically shaped nodal line centered at the $S$ HSP, as shown in Fig. 4(b). To clearly illustrate this further, Fig. 4(c) shows a contour plot of the energy of the lower band, that is intersecting a higher energy band, as a function of $k_y$ and $k_z$. In addition, Fig. 4(d) gives a contour plot of the energy-difference between these two intersecting Dirac cones. Notice that the energy differ-
ence between the upper and lower Dirac cones at the $S$ point is only $\sim 5$ meV. As a result, because the Fermi velocity is $h v_F \sim 1.13$ eVÅ along the $k_y$ direction and 0.23 eVÅ along the $k_z$-direction, the semimajor axis of the nodal line is about 0.01 Å$^{-1}$ and the semiminor axis is about 0.002 Å$^{-1}$. Therefore, a very dense $k$-point mesh was required to calculate this nodal line.

Finally, we confirm the validity of the DFT calculations through measurements of the angular dependence of the dhVAg-effect. Figure 5 (a) displays the Fourier transform of the dhVAg signal presented in Fig. S5(a), for several values of $\theta$. Each peak, observed at a given cyclotron frequency $F$, is related to a Fermi surface cross-sectional areas $A$ through the Onsager relation $F = \hbar A/2\pi e$. Therefore, in Fig. 5 (b), upper and lower panels, we superimpose the $F$s extracted from the Fourier spectra in (a) (black crosses), with the $F$s expected from the Fermi surface cross-sectional areas (colored markers). Given the large number of $\alpha$-orbits observed between 0.5 and 2.0 kT it is not possible to track their exact angular dependence, but one obtains a very good overlap between the predicted and the observed orbits in this frequency range. Nevertheless, discrepancies are observed at lower frequencies that are likely ascribable to the intrinsic errors associated with any specific DFT implementation. In Fig. S5(b) we included the amplitude of the peaks observed in the FFT spectra as a function of the temperature damping factor in the Lifshitz-Kosevich formalism.

In summary, we have shown here, through a group theory analysis and DFT calculations, that the lower temperature phase of RhSi, i.e., the orthorhombic $\alpha$-RhSi, is also topological in character. It preserves roto-inversion symmetry and, therefore, instead of being a multifold Weyl fermion system as $\beta$-RhSi, it is a unique example of a Dirac semimetallic system, displaying single, as well as double Dirac nodes in close proximity to the Fermi level (within 100 and 150 meV from $\varepsilon_F$). The double Dirac dispersions, emerging from the $S$-point with only 5 meV distance between the corresponding pair of Dirac points, intersect forming a nodal line in the $k_y - k_z$-plane protected by the nonsymmorphic symmetry of $\alpha$-RhSi. This double Dirac structure and the associated Dirac nodal line is similar to what was proposed for the correlated iridate CaIrO$_3$.$^{44,48}$ However, in contrast to CaIrO$_3$, orthorhombic $\alpha$-RhSi does not display topologically trivial bands intersecting $\varepsilon_F$; all bands crossing $\varepsilon_F$ emerge directly from the Dirac nodes. Electronic correlations might be relevant also to $\alpha$-RhSi explaining perhaps the mild deviations observed between calculated and experimentally determined Fermi surface cross-sectional areas. Measurements of the de Haas-van Alphen effect in high quality flux grown single-crystals, reveal a Fermi surface whose topography is in good agreement with the DFT predictions, thus, validating the band structure calculations. The anomalous behavior of the magnetic torque observed for certain field orientations points to the possibility of transitions between distinct topological regimes as the Zeeman-effect displaces the spin-orbit split bands and lifts the Kramers degeneracy of the two Dirac dispersions.

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